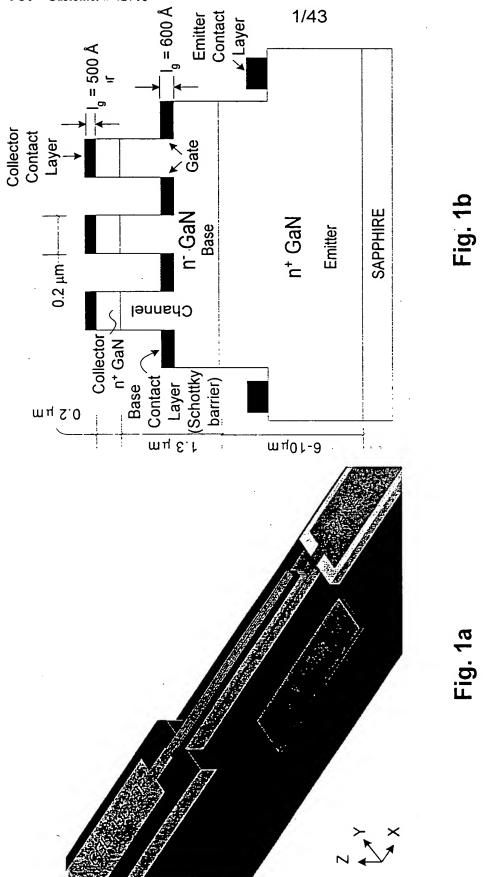
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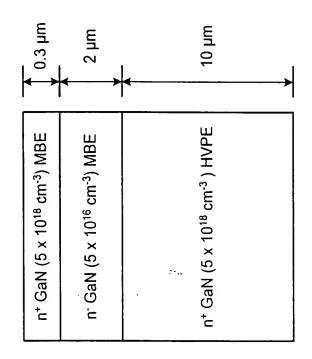
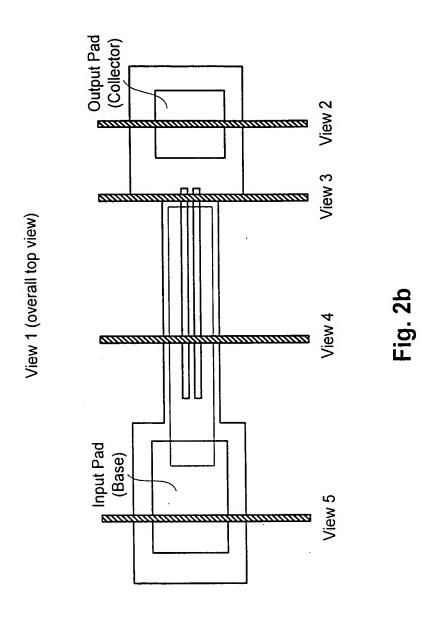
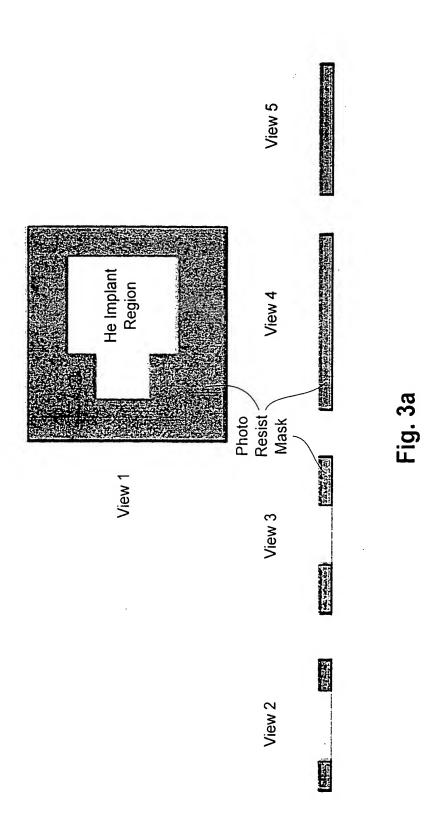


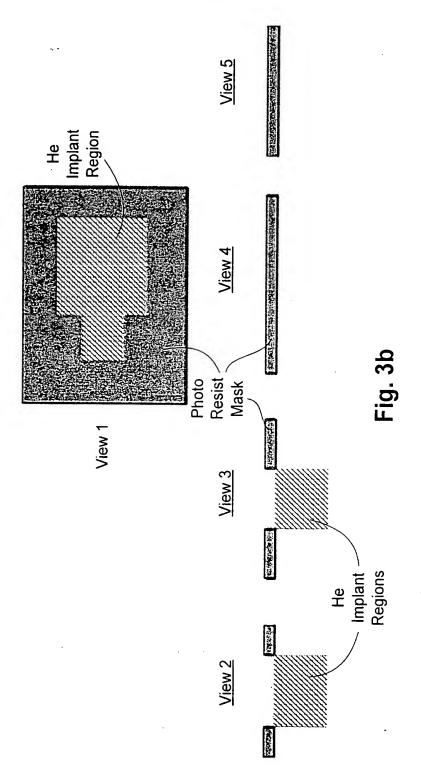
Fig. 2a



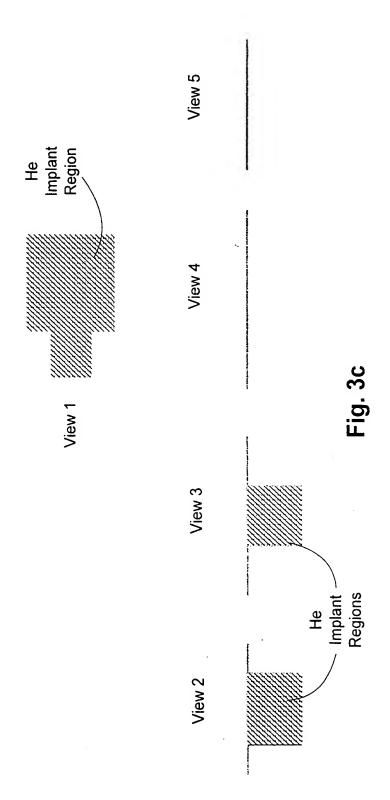
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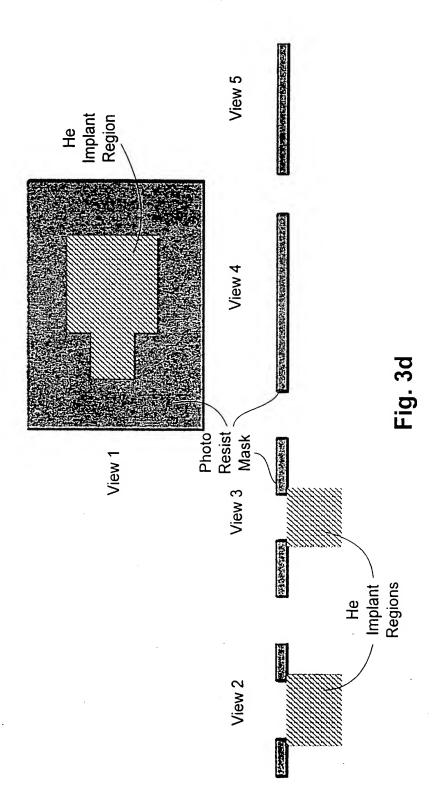
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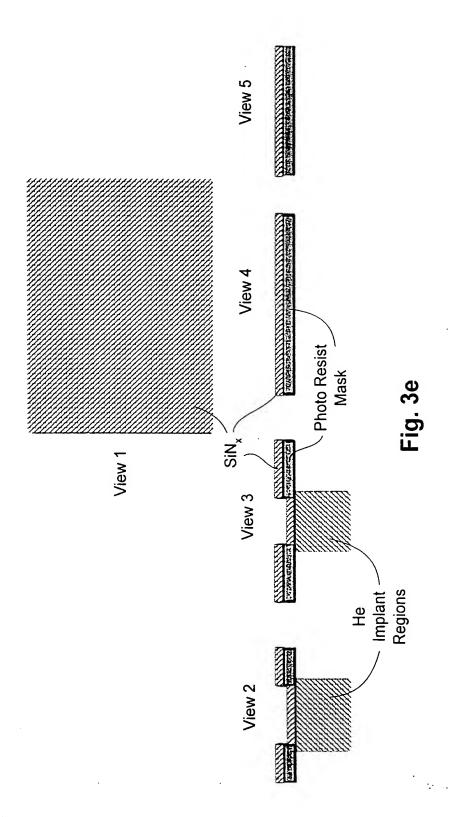
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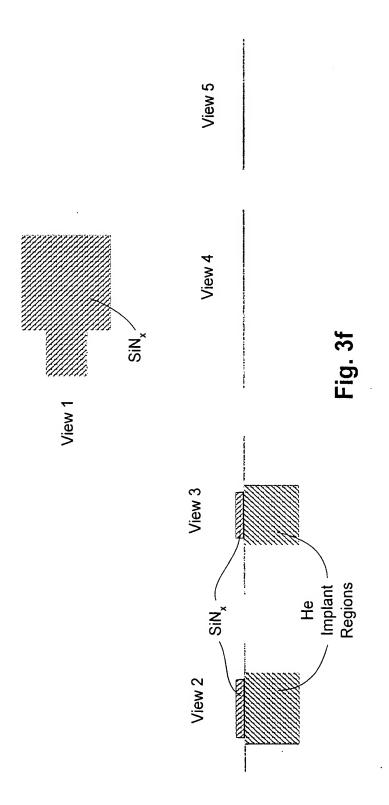
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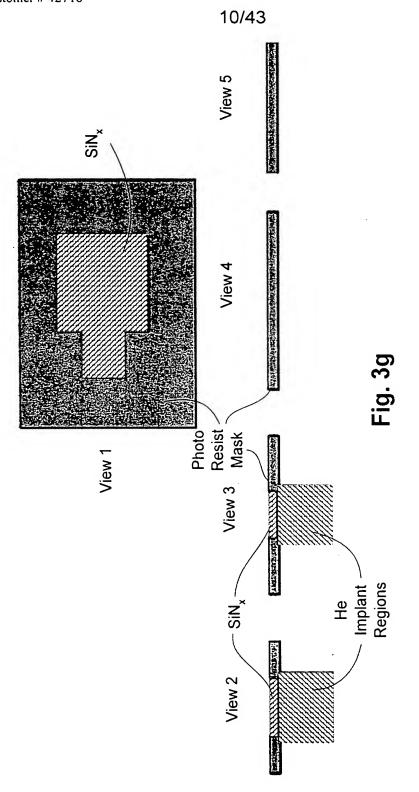
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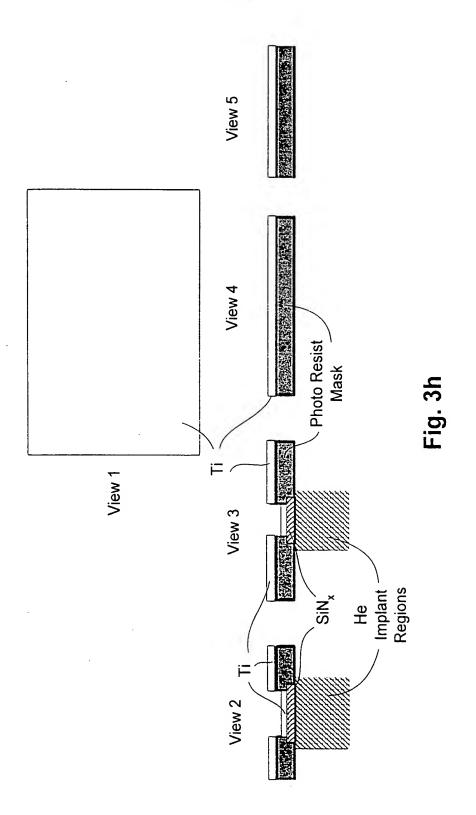
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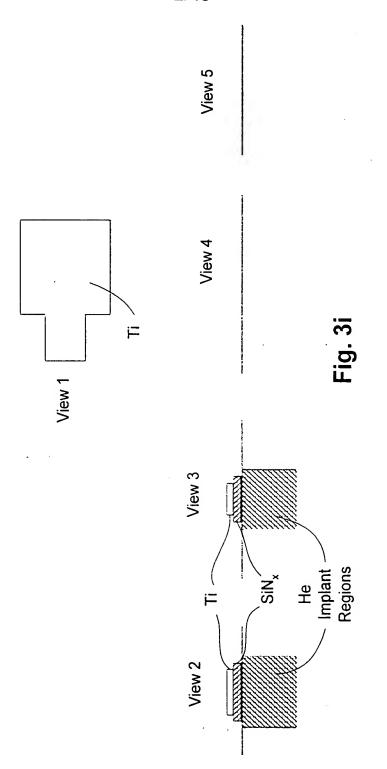
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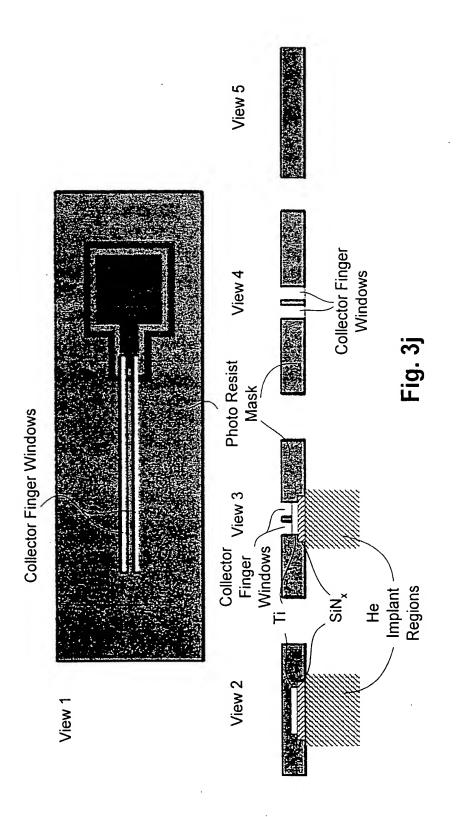
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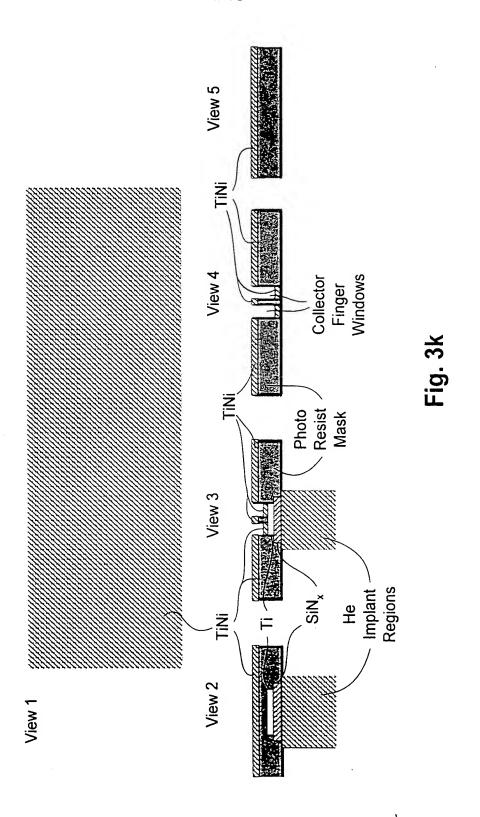


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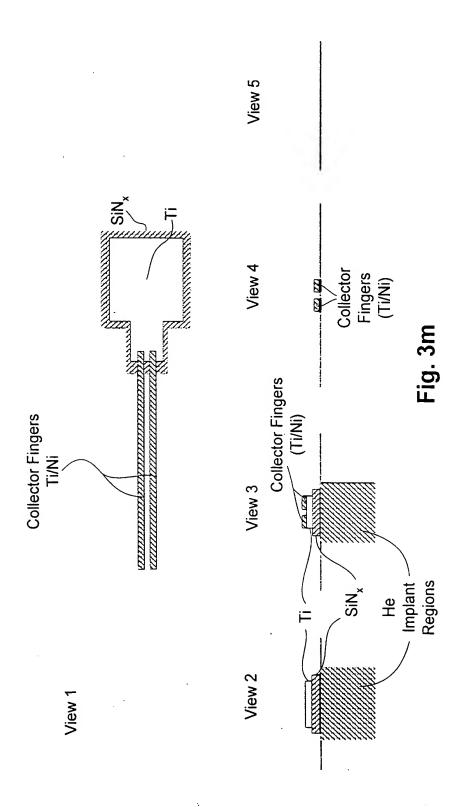


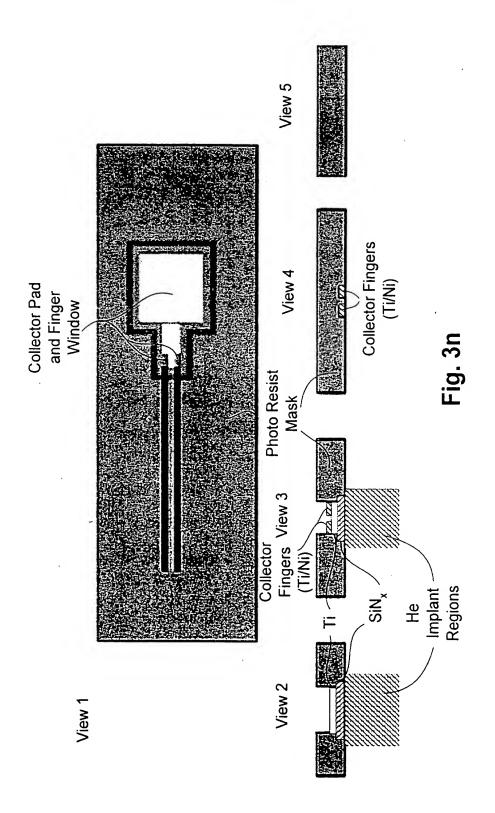
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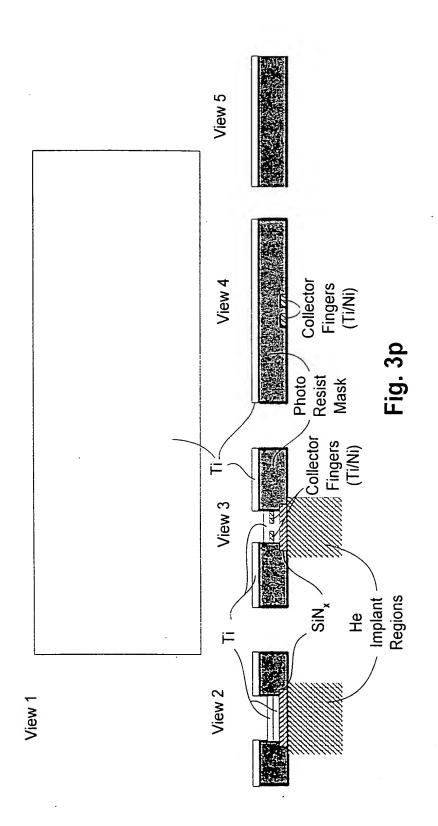


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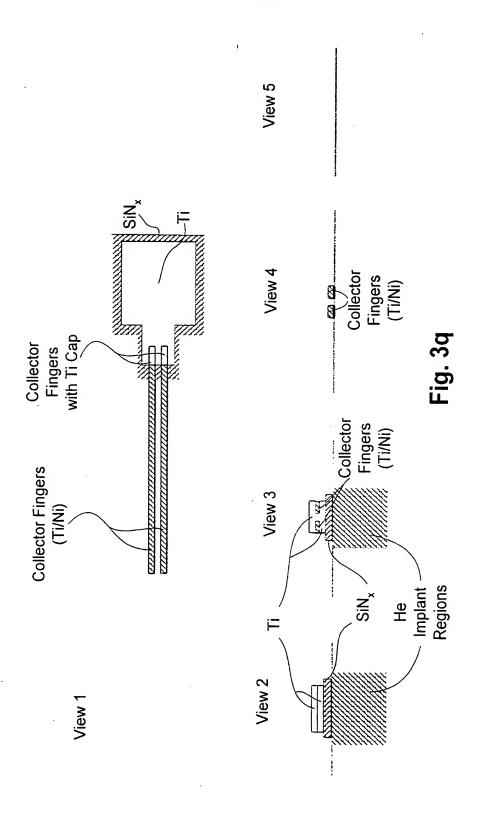




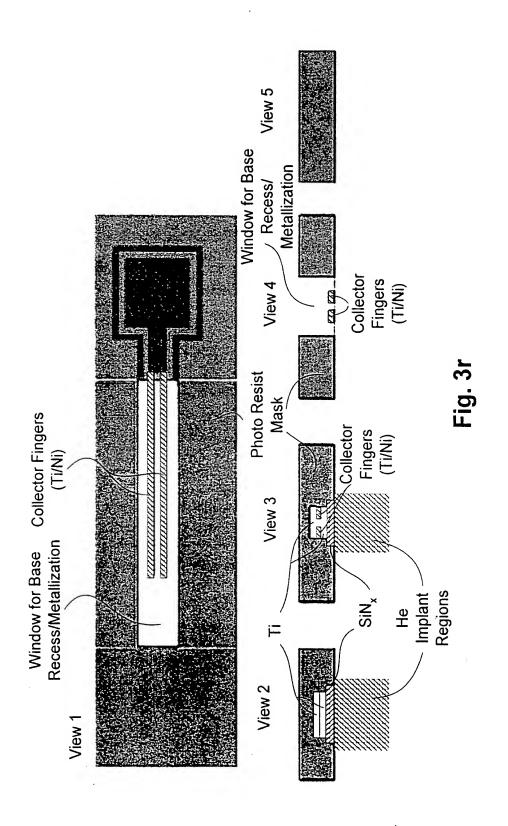
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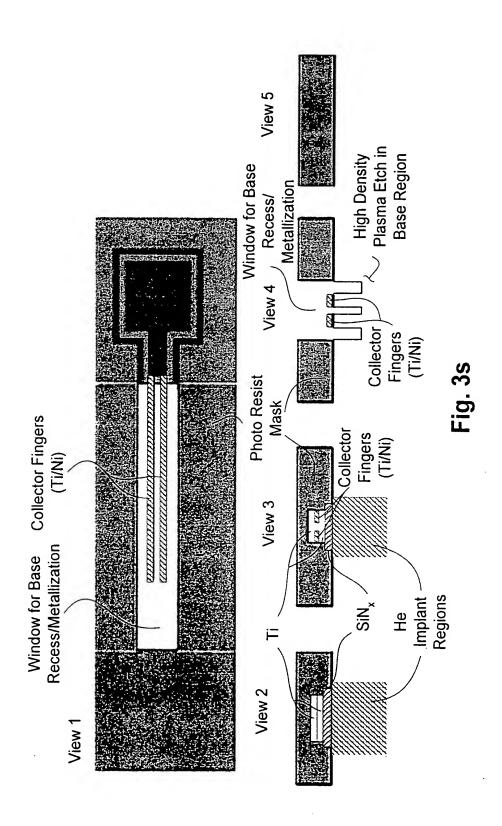
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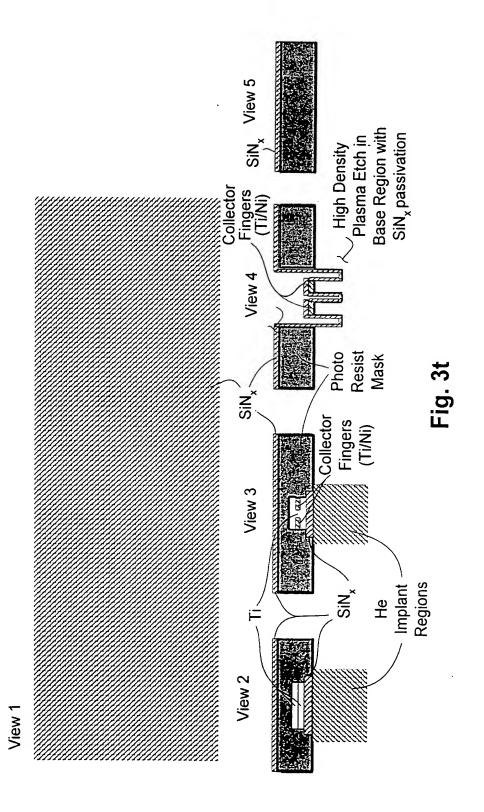
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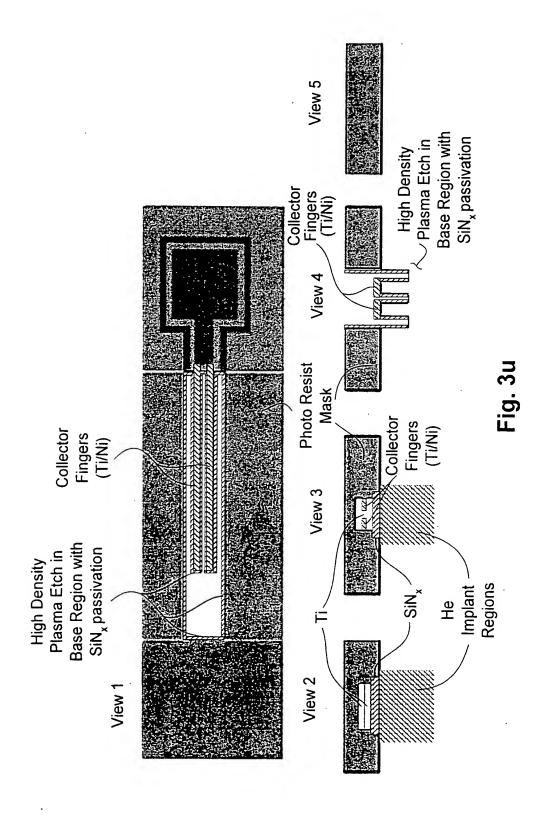
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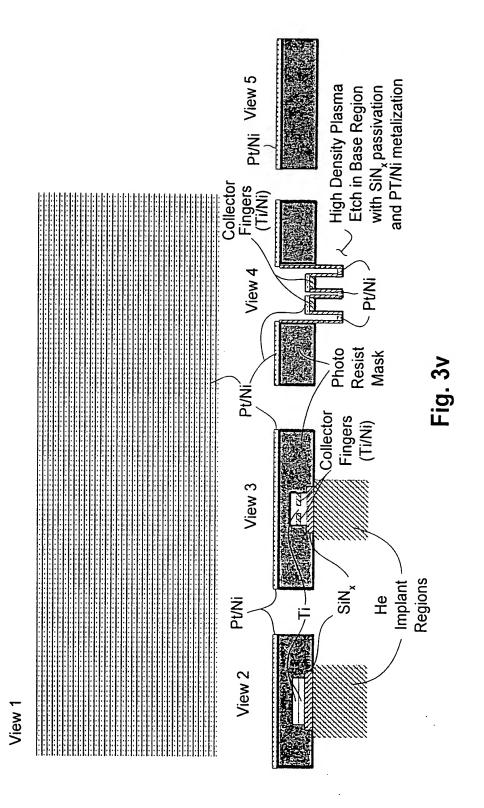
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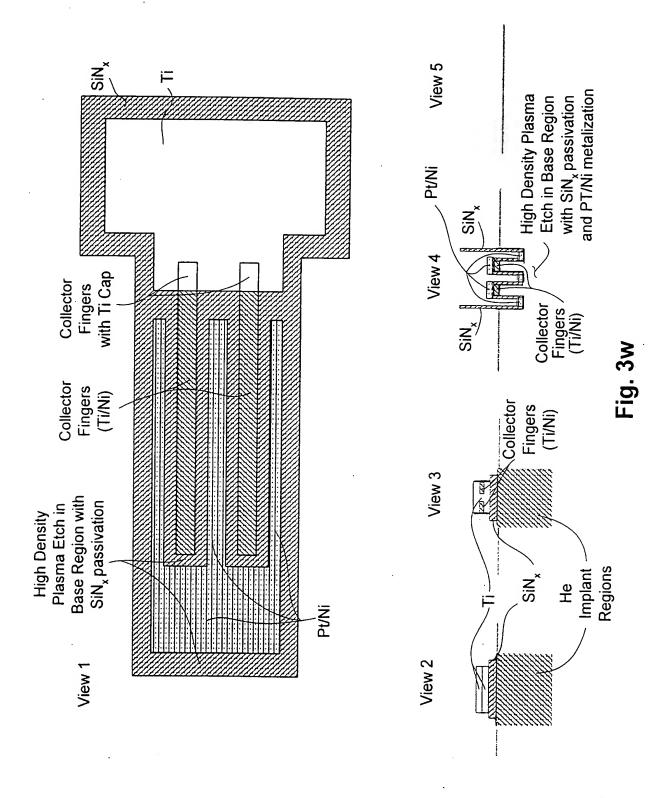
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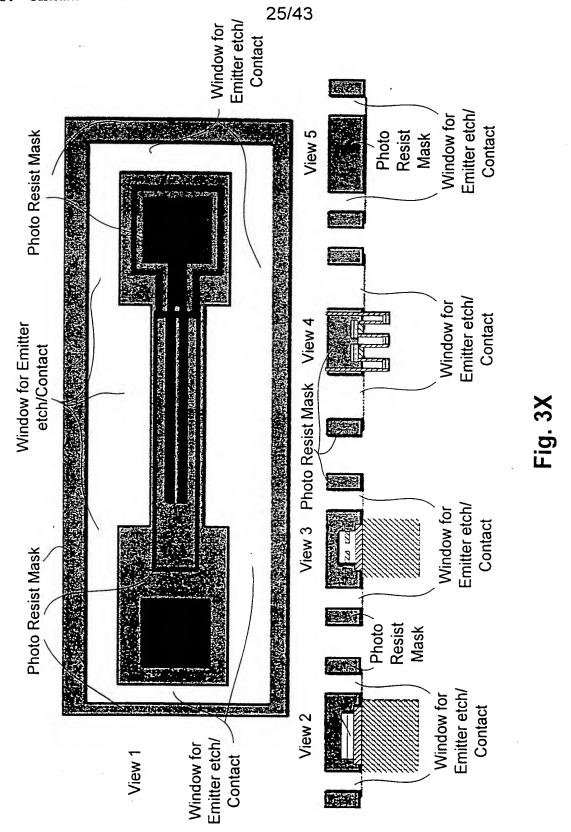
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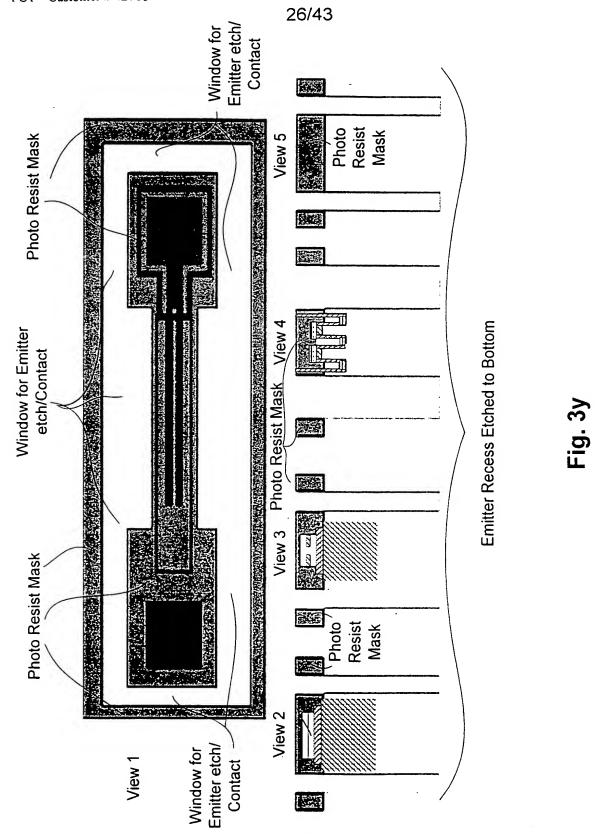
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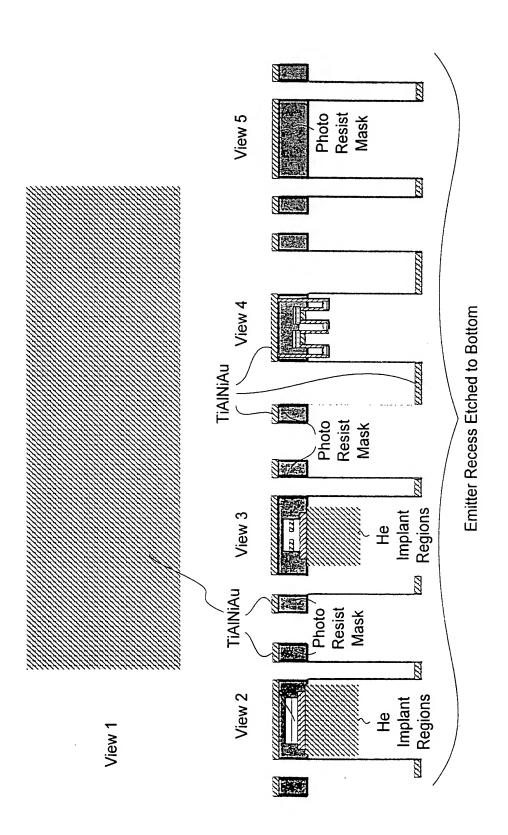
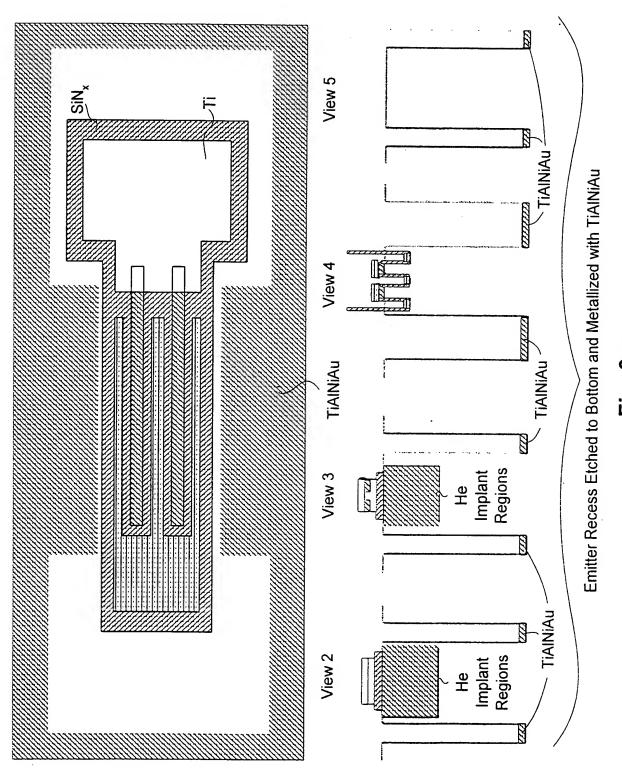


Fig. 3z

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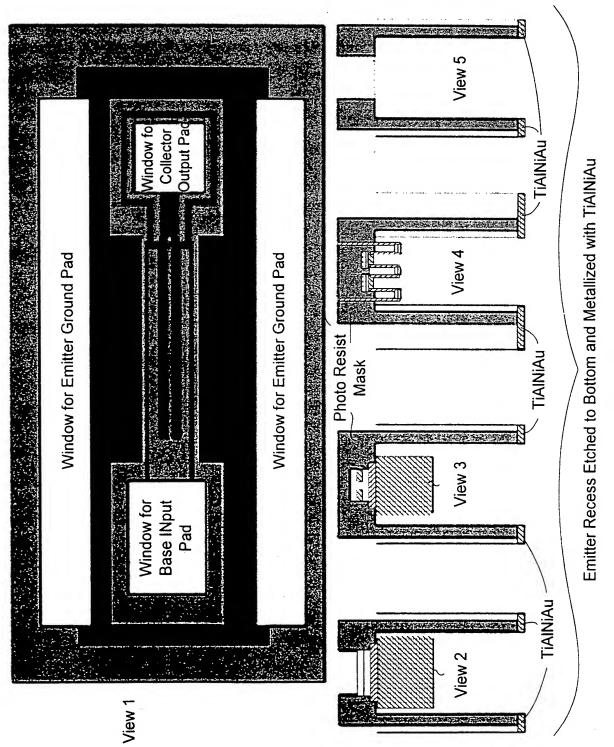


Fig. 3bb

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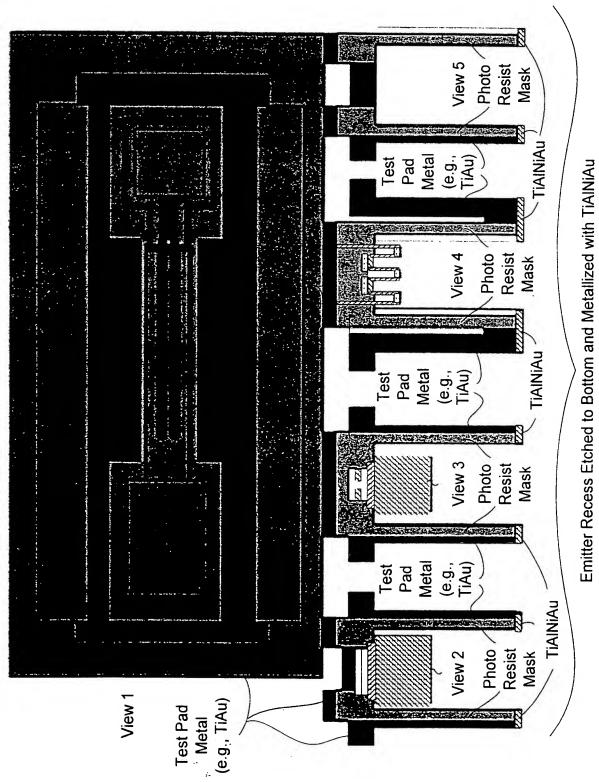
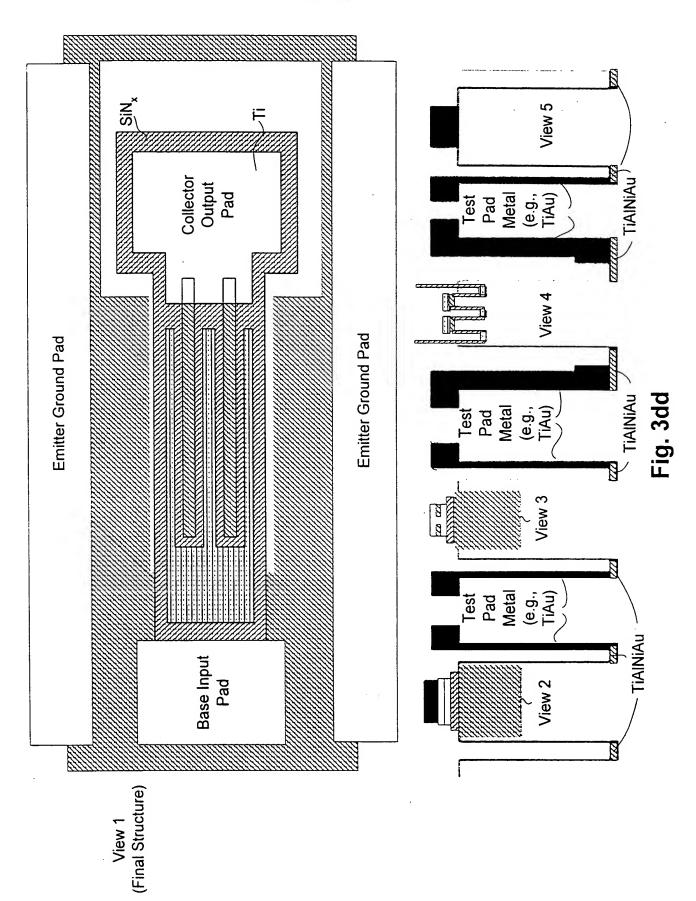


Fig. 3cc

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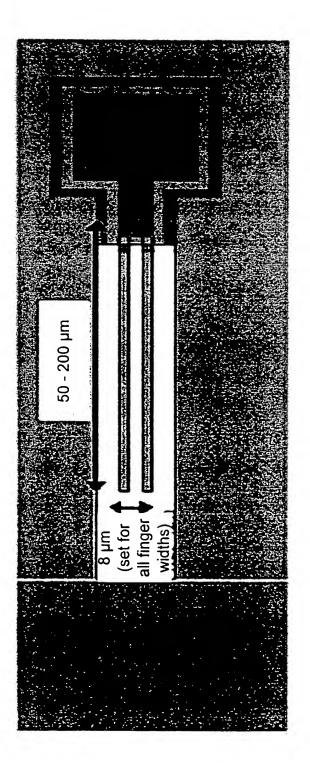
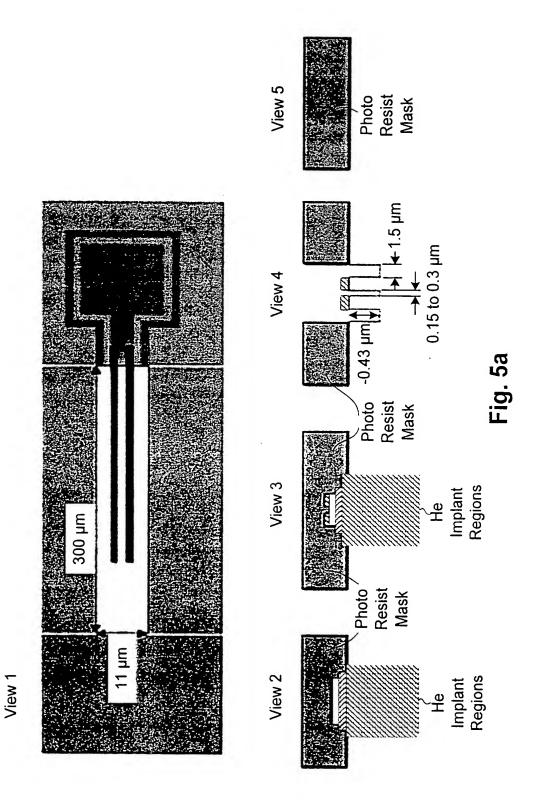


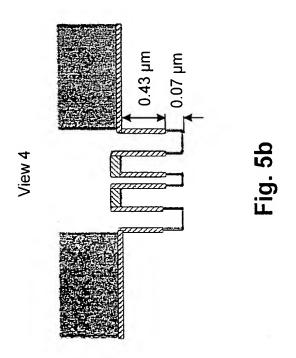
Fig. 4

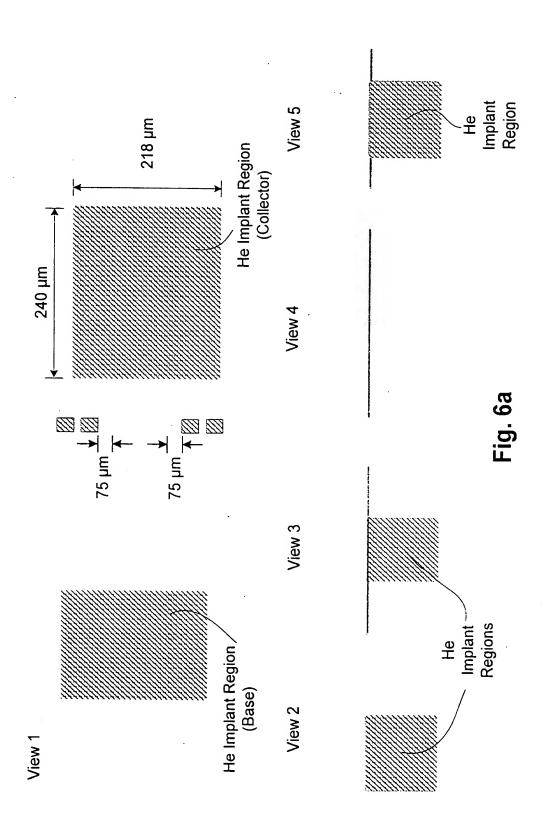
View 1

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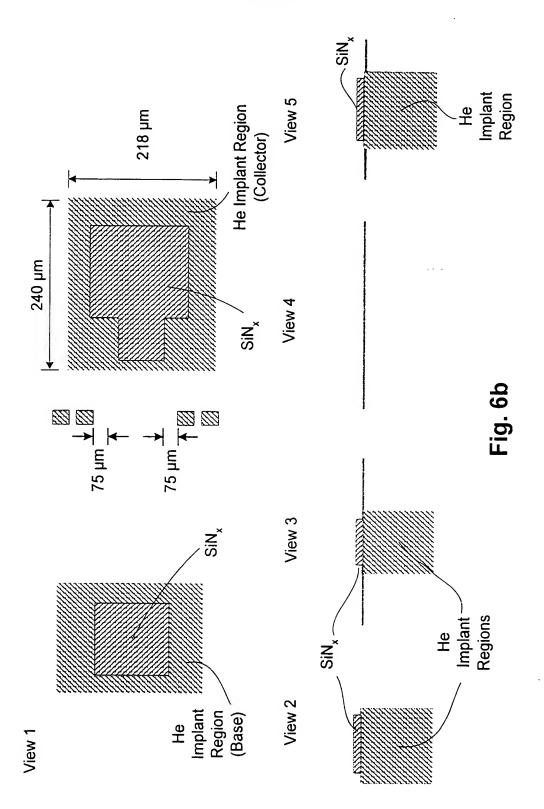


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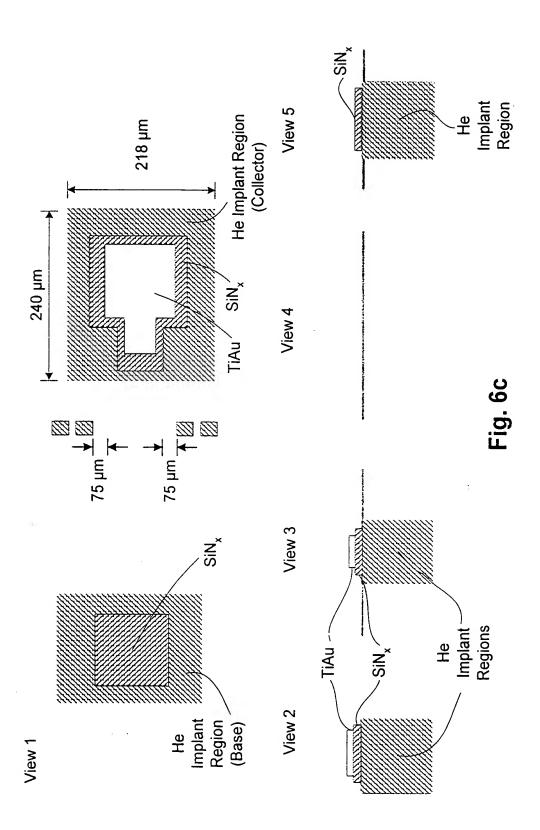




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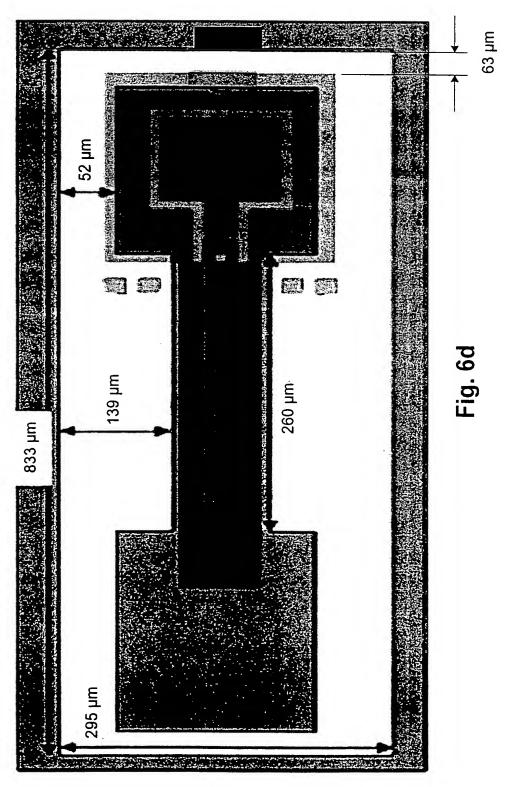


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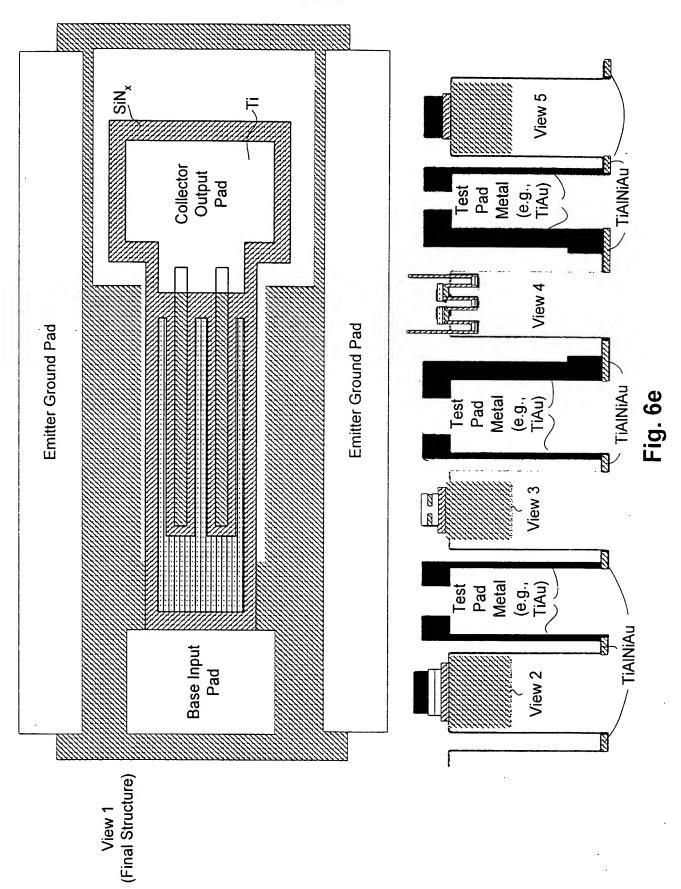


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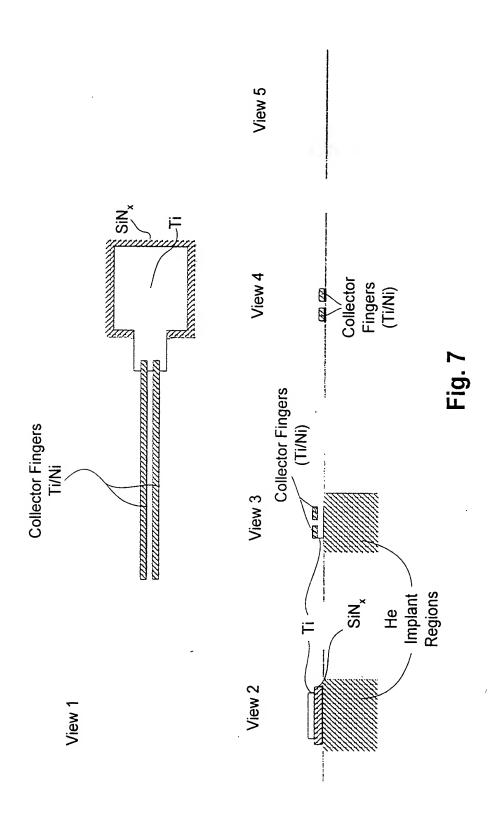
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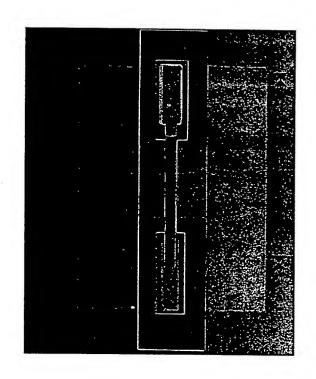
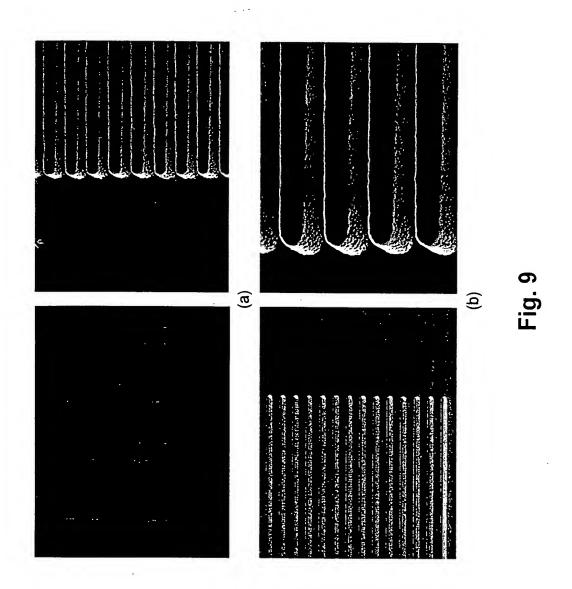
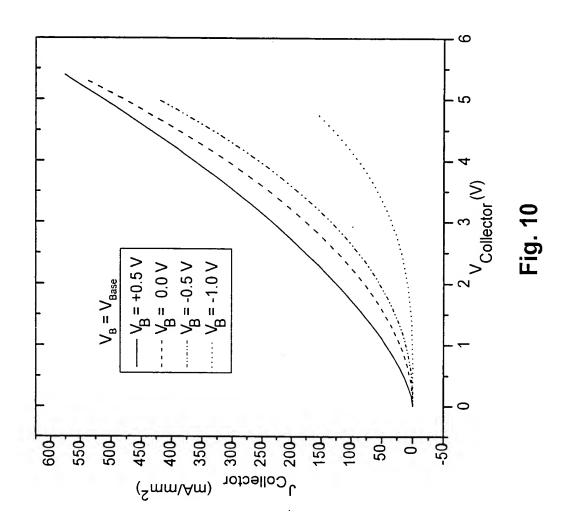


Fig. 8

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